TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC2235

Audio Power Amplifier Applications
Driver Stage Amplifier Applications

• Complementary to 2SA965.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V _{CEO}	120	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	800	mA
Base current	lΒ	80	mA
Collector power dissipation	P _C	900	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	−55 to 150	°C

O.75MAX.

O.75MAX.

O.8MAX.

O.6MAX.

O.6MAX.

O.6MAX.

O.6MAX.

O.75MAX.

O

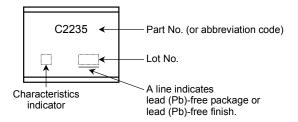
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

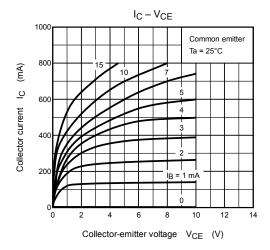
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 120 V, I _E = 0	_	_	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	100	nA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	120	_	_	٧
Emitter-base breakdown voltage	V (BR) EBO	I _E = 1 mA, I _C = 0	5	_	_	V
DC current gain	h _{FE} (Note)	V _{CE} = 5 V, I _C = 100 mA	80	_	240	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 500 mA, I _B = 50 mA	_	_	1.0	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 500 mA	_	_	1.0	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 100 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	_	30	pF

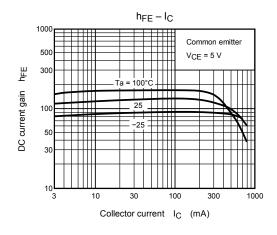
Note: hFE classification O: 80 to 160, Y: 120 to 240

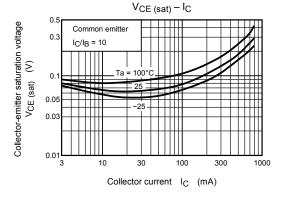
Marking

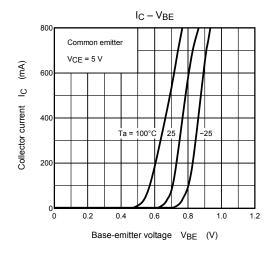


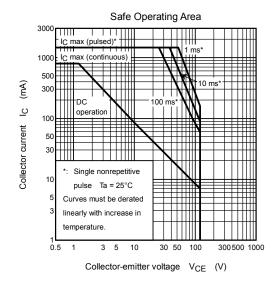
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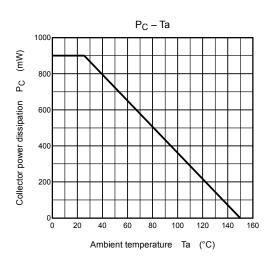












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